

Linear Systems replaces discontinued Siliconix J211

The LSJ211 is a n-channel JFET General Purpose amplifier with low noise and low leakage.

The SOT-23 package is well suited for cost sensitive applications and mass production.

(See Packaging Information).

LSJ211 Benefits:

- High gain
- Low Leakage
- Low Noise

LSJ211 Applications:

- General Purpose Amplifiers
- UHF / VHF Amplifiers
- Mixers
- Oscillators

FEATURES

DIRECT REPLACEMENT FOR SILICONIX J211

HIGH GAIN $g_{fs} = 7000 \mu mho$ MIN

HIGH INPUT IMPEDANCE $I_{GSS} = 100 pA$ max

LOW INPUT CAPACITANCE $C_{iss} = 5 pF$

ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted)

Maximum Temperatures

Storage Temperature $-55^{\circ}C$ to $+150^{\circ}C$

Operating Junction Temperature $-55^{\circ}C$ to $+135^{\circ}C$

Maximum Power Dissipation

Continuous Power Dissipation 360mW

Derating over temperature 3.27 mW/°C

MAXIMUM CURRENT

Gate Current (Note 1) 10mA

MAXIMUM VOLTAGES

Gate to Drain Voltage or Gate to Source Voltage -25V

LSJ211 ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	TYP.	MAX	UNITS	CONDITIONS
BV_{GSS}	Gate to Source Breakdown Voltage	-25	--	--	V	$V_{DS} = 0V, I_G = -1 \mu A$
$V_{GS(off)}$	Gate to Source Cutoff Voltage	-2.5	--	-4.5	V	$V_{DS} = 15V, I_D = 1nA$
I_{DSS}	Drain to Source Saturation Current (Note 2)	7	--	20	mA	$V_{DS} = 15V, V_{GS} = 0V$
I_{GSS}	Gate Reverse Current (Note 3)	--	--	-100	pA	$V_{DS} = 0V, V_{GS} = -15V$
I_G	Gate Operating Current (Note 3)	--	-10	--	pA	$V_{DS} = 10V, I_D = 1mA$
$r_{DS(on)}$	Drain to Source On Resistance	--	--	50	Ω	$I_G = 1mA, V_{DS} = 0V$

LSJ211 DYNAMIC ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	TYP.	MAX	UNITS	CONDITIONS
g_{fs}	Forward Transconductance	6000	--	12000	μmho	$V_{DS} = 15V, V_{GS} = 0V, f = 1kHz$
g_{os}	Output Conductance	--	--	200	μmho	$V_{DS} = 15V, V_{GS} = 0V, f = 1kHz$
C_{iss}	Input Capacitance	--	4	--	pF	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$
C_{rss}	Reverse Transfer Capacitance	--	1	--	pF	$V_{DS} = 15V, V_{GS} = 0V, f = 1kHz$
e_n	Equivalent Noise Voltage	--	10	--	nV/√Hz	$V_{DS} = 15V, V_{GS} = 0V, f = 1kHz$

LSJ211 SWITCHING CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	UNITS	CONDITIONS
$t_{d(on)}$	Turn On Time	2	$V_{DD} = 10V$ $V_{GS(H)} = 0V$
t_r	Turn On Rise Time	2	See Switching Circuit
$t_{d(off)}$	Turn Off Time	6	
t_f	Turn Off Fall Time	15	

Note 1 - Absolute maximum ratings are limiting values above which LSJ211 serviceability may be impaired.

Note 2 - Pulse test duration = 2ms

Note 3 - Approximately doubles for every 10°C increase in T_A

Micross Components Europe

Available Packages:

SOT-23 (Top View)



LSJ211 in SOT-23
LSJ211 in bare die.

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Please contact Micross for full package and die dimensions

